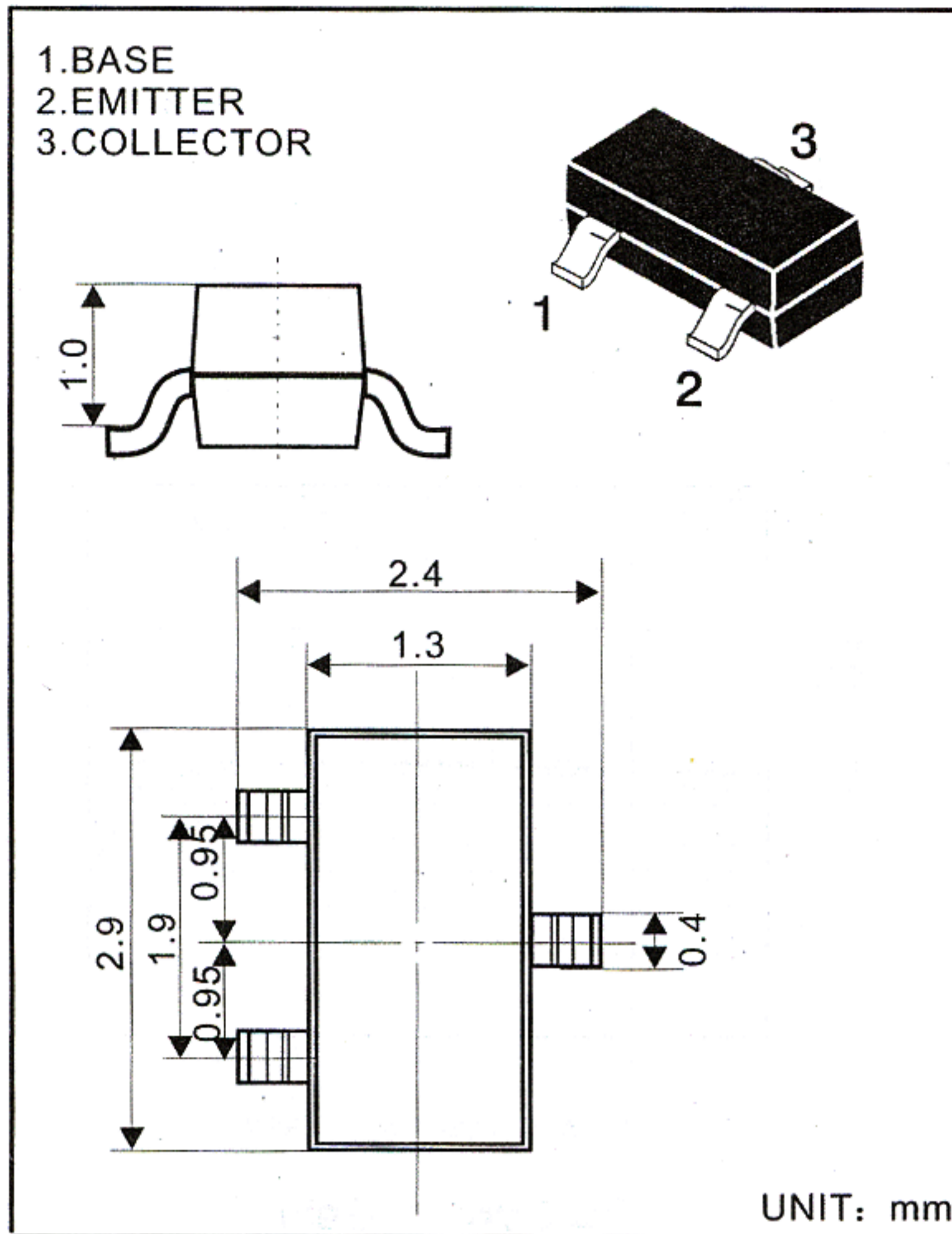


S9018LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 25V

Operating and storage junction temperature range

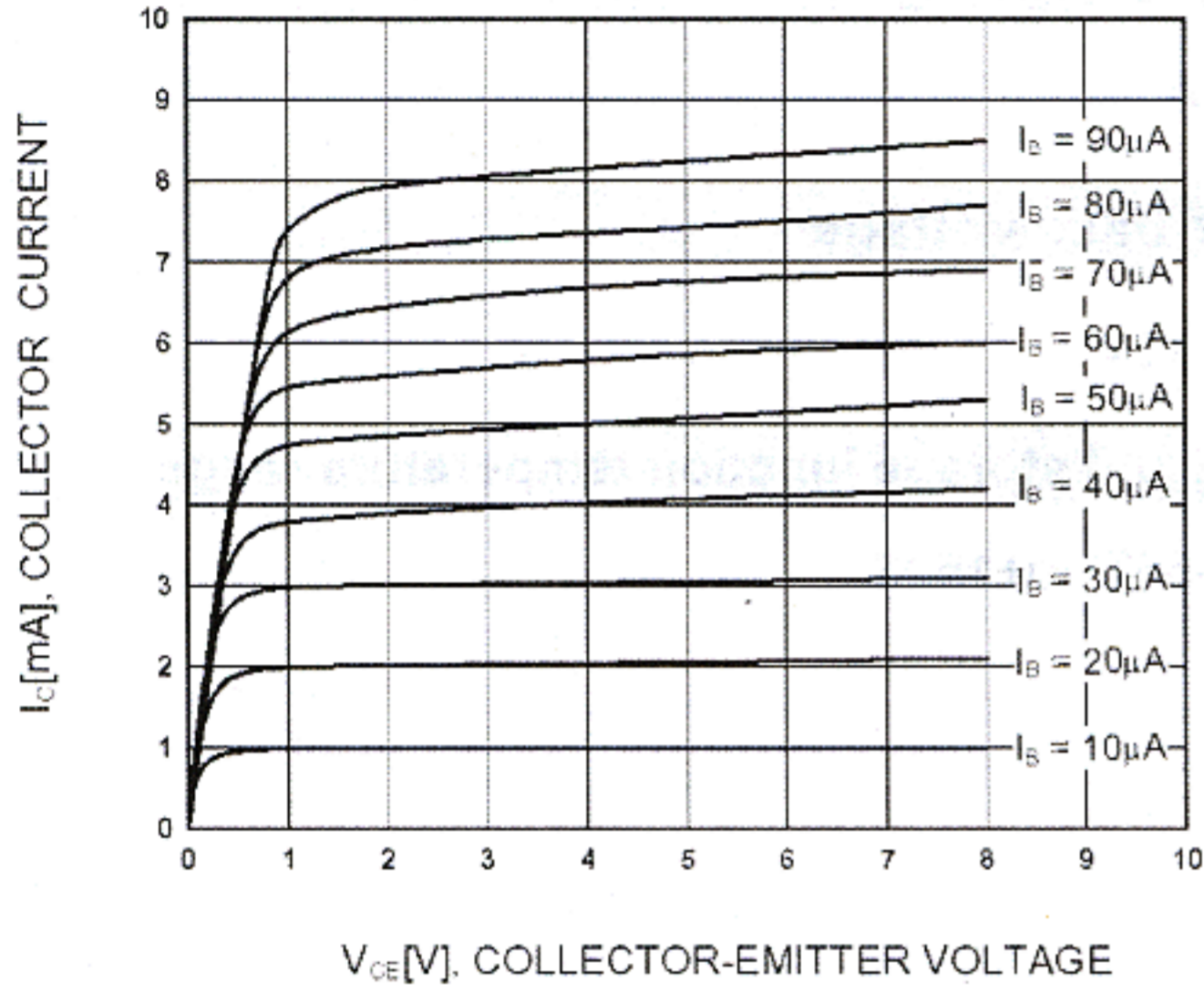
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

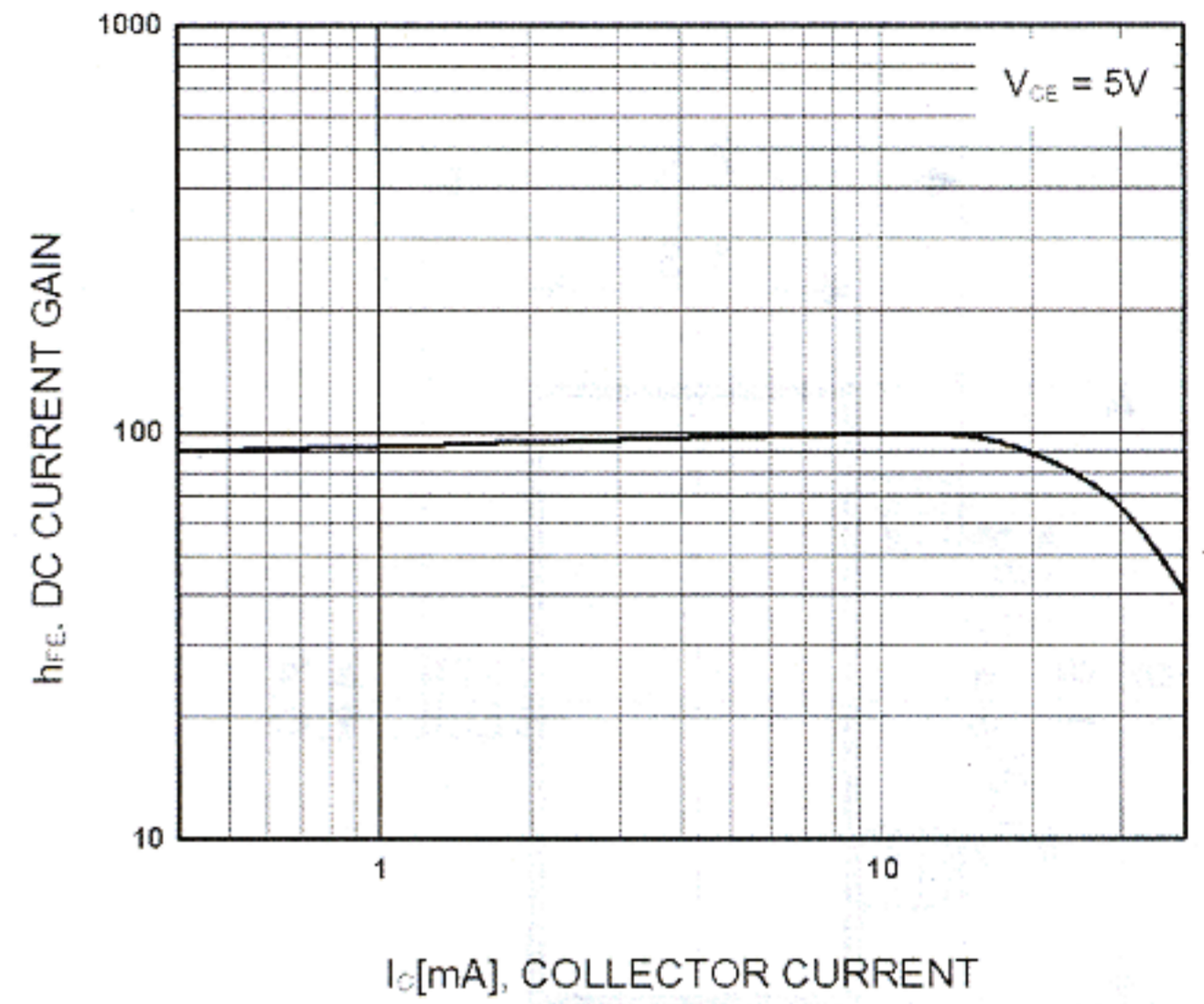
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=15V, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0mA$			0.1	μA
DC current gain	H_{FE}	$V_{CE}=5V, I_C=1mA$	70		190	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=10mA, I_B=1mA$			0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=10mA, I_B=5mA$			1.4	V
Transition frequency	f_T	$V_{CE}=5V, I_C=5mA$ $f=400MHz$	600			MHz

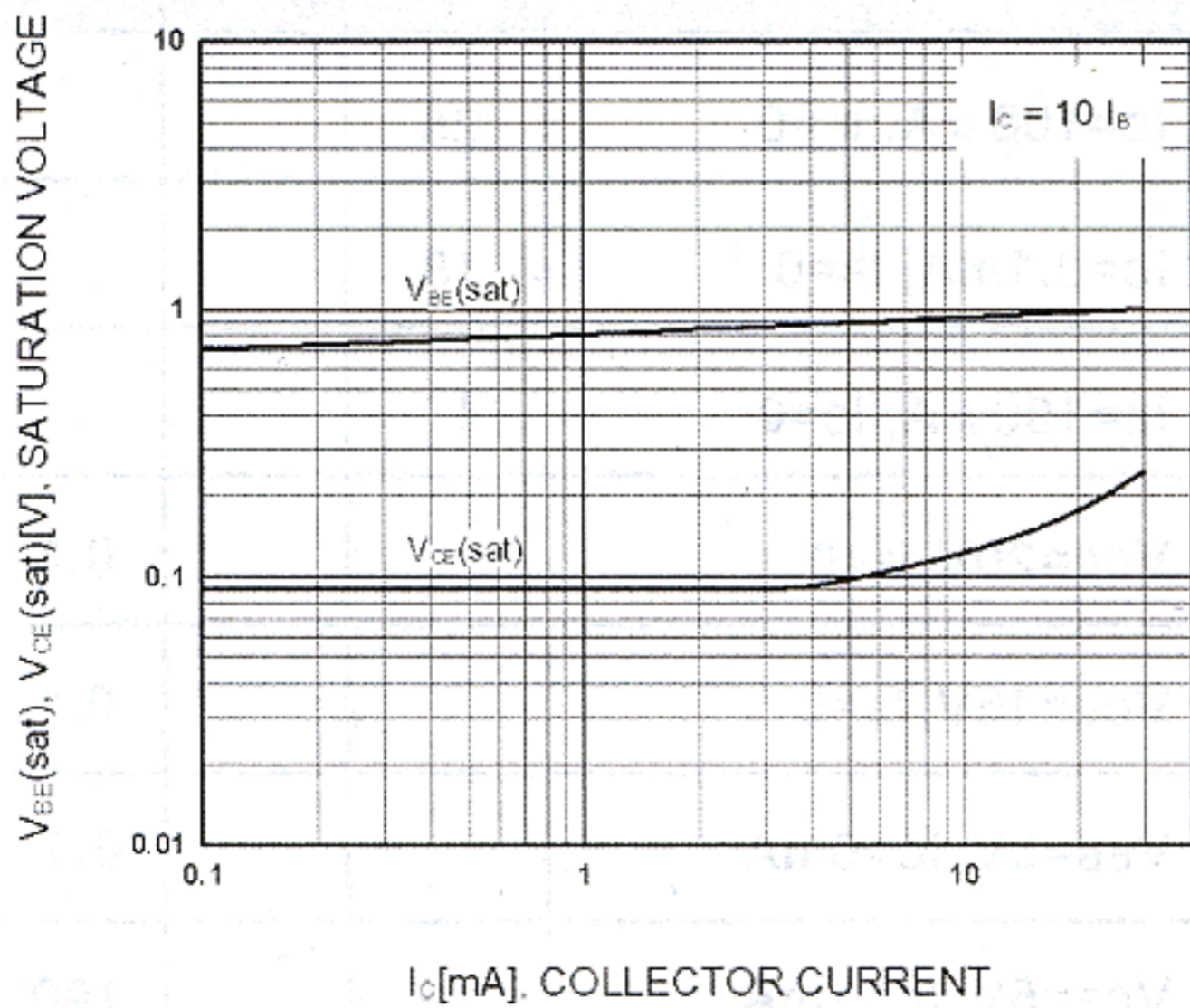
DEVICE MARKING : S9018LT1=J8



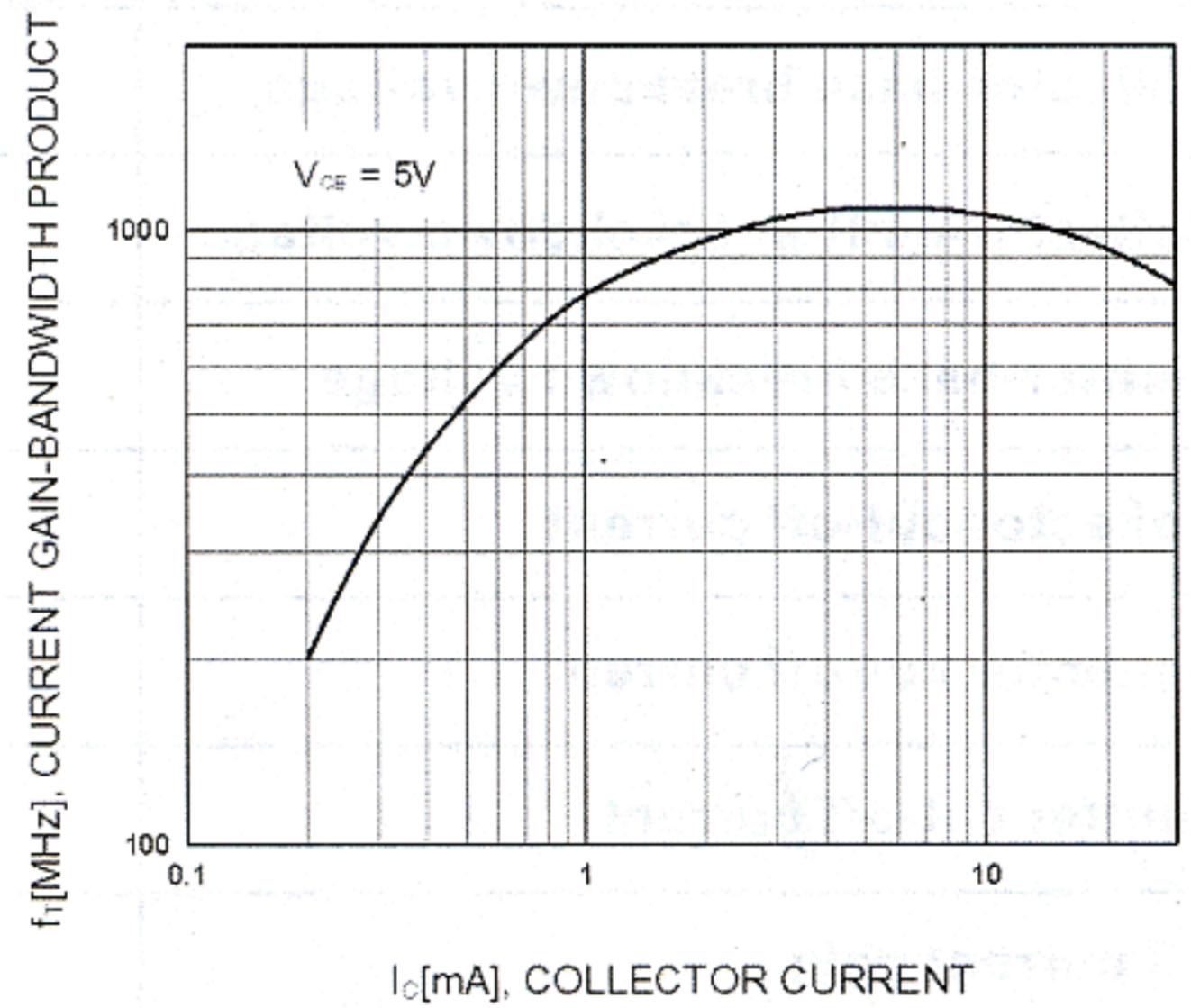
Static Characteristic



DC Current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product